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1. Document ID: US 5592501 A

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TITLE: Group III nitride laser structure - formed on a conductive silicon carbide

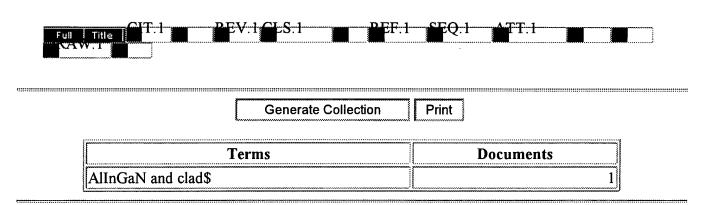
substrate

Basic Abstract Text:

A separate-confinement heterostructure laser comprises: an InGaN active layer; upper and lower waveguide layers on the active layer formed from the group consisting of AlGaN, InGaN, and AlInGaN; upper and lower cladding layers on the respective upper and lower waveguide layers and formed of AlGaN.

Basic Abstract Text (1):

A separate-confinement heterostructure laser comprises: an InGaN active layer; upper' and lower waveguide layers on the active layer formed from the group consisting of AlGaN, InGaN, and AlInGaN; upper and lower cladding layers on the respective upper and lower waveguide layers and formed of AlGaN.



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Previous Page

Next Page